MSKSEMI















ESD

TVS

TSS

MOV

GDT

PLED

Broduct data sheet





SOT - 23



- 1. BASE
- 2. EMITTER
- 3. COLLECTOR

TRANSISTOR (NPN)

FEATURE

- Excellent h_{FE} Linearity
- Low noise
- Complementary to A733-MS

MARKING:CR

MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	60	V
V _{CEO}	Collector-Emitter Voltage	50	V
V _{EBO}	Emitter-Base Voltage	5	V
Ic	Collector Current -Continuous	150	mA
Pc	Collector Power Dissipation	200	mW
TJ	Junction Temperature	150	℃
T _{stg}	Storage Temperature	-55-150	℃

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

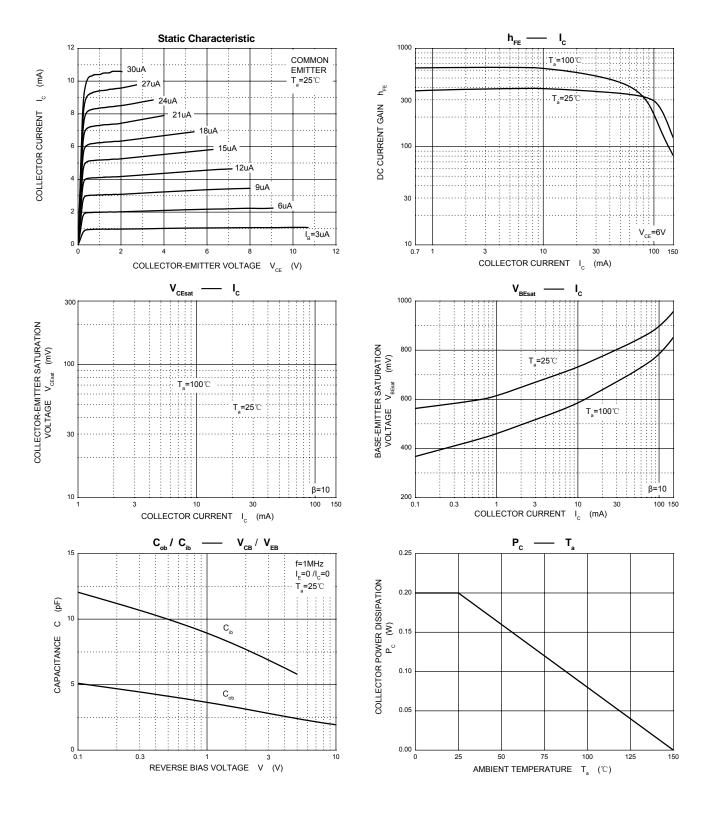
Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =100uA, I _E =0	60			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	$I_C=1$ mA , $I_B=0$	50			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =0.1mA, I _C =0	5			V
Collector cut-off current	I _{CBO}	V _{CB} =60V, I _E =0			0.1	uA
Collector cut-off current	I _{CER}	V_{CE} =55 V , R =10 $M\Omega$			0.1	uA
Emitter cut-off current	I _{EBO}	V _{EB} =5V , I _C =0			0.1	uA
DC current sein	h _{FE(1)}	V _{CE} =6 V , I _C =1mA	130		400	
DC current gain	h _{FE(2)}	V _{CE} =6 V , I _C =0.1mA	40			
Collector-emitter saturation voltage	V _{CE} (sat)	I _C =100mA, I _B =10mA			0.3	V
Base-emitter saturation voltage	V _{BE} (sat)	I _C =100mA, I _B =10mA			1	V
Transition frequency	f _T	V _{CE} =6V,I _C =10mA,f =30 MHz	150			MHz
Collector output capacitance	C _{ob}	V _{CB} =10V,I _E =0,f=1MH _Z			3.0	pF
Noise figure	NF	VCE=6V,Ic=0.1mA	4		10	dB
Noise figure	INF	$R_g=10k\Omega,f=1kMHz$		-	10	uБ

CLASSIFICATION OF h_{FE(1)}

Rank L		Н		
Range	130-200	300-400		

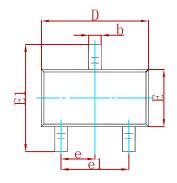


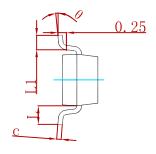
Typical Characteristics

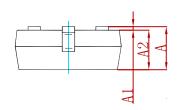




PACKAGE MECHANICAL DATA

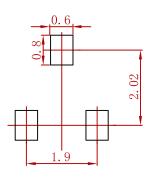






Symbol	Dimensions In Millimeters		Dimensions In Inches		
Symbol	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
Е	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

Suggested Pad Layout



- 1.Controlling dimension:in millimeters.2.General tolerance:± 0.05mm.3.The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
C945-MS	SOT-23	3000



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